

BAS21VD High-voltage switching diodes 1 August 2013

**Product data sheet** 

## 1. General description

Triple high-voltage switching diodes, encapsulated in a SOT457 (SC-74/TSOP6) small Surface-Mounted Device (SMD) plastic package.

## 2. Features and benefits

- High switching speed: t<sub>rr</sub> ≤ 50 ns
- Low capacitance: C<sub>d</sub> ≤ 5 pF
- Reverse voltage: V<sub>R</sub> ≤ 200 V
- AEC-Q101 qualified
- Repetitive peak reverse voltage: V<sub>RRM</sub> ≤ 250 V
- Repetitive peak forward current: I<sub>FRM</sub> ≤ 1 A
- Small SMD plastic package

## 3. Applications

- · High-voltage switching in surface-mounted circuits
- Automotive
- Communication

## 4. Quick reference data

| Table 1. Quick reference data |                       |  |     |     |     |     |      |
|-------------------------------|-----------------------|--|-----|-----|-----|-----|------|
| Symbol                        | Parameter             | Conditions   |     | Min | Тур | Max | Unit |
| Per diode                     |                       |  |     |     |     |     |      |
| l <sub>F</sub>                | forward current       | pulsed; $t_p \le 300 \ \mu s; \ \delta \le 0.02$   | [1] | -   | -   | 200 | mA   |
| V <sub>R</sub>                | reverse voltage       |  |     | -   | -   | 200 | V    |
| Per diode                     |                       |  |     |     |     |     |      |
| I <sub>R</sub>                | reverse current       | $V_R$ = 200 V; T <sub>amb</sub> = 25 °C; pulsed;<br>t <sub>p</sub> ≤ 300 μs; δ ≤ 0.02  |     | -   | 25  | 100 | nA   |
| t <sub>rr</sub>               | reverse recovery time | I <sub>F</sub> = 30 mA; I <sub>R</sub> = 30 mA; I <sub>R(meas)</sub> = 3 mA;<br>R <sub>L</sub> = 100 Ω; T <sub>amb</sub> = 25 °C |     | -   | 16  | 50  | ns   |

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.





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## 5. Pinning information

| Table 2. | Pinning | information       |                    |                    |
|----------|---------|-------------------|--------------------|--------------------|
| Pin      | Symbol  | Description       | Simplified outline | Graphic symbol     |
| 1        | K1      | cathode (diode 1) |                    | 6 5 4              |
| 2        | K2      | cathode (diode 2) |                    |                    |
| 3        | K3      | cathode (diode 3) |                    |                    |
| 4        | A3      | anode (diode 3)   | TSOP6 (SOT457)     |                    |
| 5        | A2      | anode (diode 2)   |                    | 1 2 3<br>006aab241 |
| 6        | A1      | anode (diode 1)   |                    | 000880241          |

# 6. Ordering information

| Table 3. Ordering information |         |  |         |  |  |
|-------------------------------|---------|--|---------|--|--|
| Type number                   | Package |  |         |  |  |
|                               | Name    | Description                                      | Version |  |  |
| BAS21VD                       | TSOP6   | plastic surface-mounted package (TSOP6); 6 leads | SOT457  |  |  |

## 7. Marking

| Table 4. Marking codes |              |
|------------------------|--------------|
| Type number            | Marking code |
| BAS21VD                | B5           |

# 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol           | Parameter                       | Conditions   |     | Min | Max | Unit |
|------------------|---------------------------------|--|-----|-----|-----|------|
| Per diode        |                                 |  |     |     |     |      |
| V <sub>RRM</sub> | repetitive peak reverse voltage |  |     | -   | 250 | V    |
| V <sub>R</sub>   | reverse voltage                 |  |     | -   | 200 | V    |
| I <sub>F</sub>   | forward current                 | pulsed; $t_p \le 300 \ \mu s$ ; $\delta \le 0.02$  | [1] | -   | 200 | mA   |
| I <sub>FRM</sub> | repetitive peak forward current | t <sub>p</sub> ≤ 1 ms; δ ≤ 25 %                    |     | -   | 1   | А    |
| I <sub>FSM</sub> | non-repetitive peak forward     | $t_p$ = 10 µs; $T_{j(init)}$ = 25 °C; square wave  |     | -   | 16  | А    |
| C                | current                         | $t_p$ = 100 µs; $T_{j(init)}$ = 25 °C; square wave |     | -   | 8   | А    |
|                  |                                 | $t_p$ = 10 ms; $T_{j(init)}$ = 25 °C; square wave  |     | -   | 2   | А    |

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| Symbol           | Parameter               | Conditions               |     | Min | Max | Unit |
|------------------|-------------------------|--------------------------|-----|-----|-----|------|
| Per device;      | one diode loaded        |                          |     |     |     |      |
| P <sub>tot</sub> | total power dissipation | T <sub>amb</sub> ≤ 25 °C | [1] | -   | 250 | mW   |
|                  |                         |                          | [2] | -   | 295 | mW   |
| T <sub>stg</sub> | storage temperature     |                          |     | -65 | 150 | °C   |
| Tj               | junction temperature    |                          |     | -   | 150 | °C   |
| T <sub>amb</sub> | ambient temperature     |                          |     | -65 | 150 | °C   |

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm<sup>2</sup>.

## 9. Thermal characteristics

| Table 6.   Thermal characteristics |  |             |     |     |     |     |      |
|------------------------------------|--|-------------|-----|-----|-----|-----|------|
| Symbol                             | Parameter  | Conditions  |     | Min | Тур | Мах | Unit |
| Per device; on                     | Per device; one diode loaded                           |             |     |     |     |     |      |
| R <sub>th(j-a)</sub>               | thermal resistance                                     | in free air | [1] | -   | -   | 500 | K/W  |
|                                    | from junction to<br>ambient                            |             | [2] | -   | -   | 425 | K/W  |
| R <sub>th(j-sp)</sub>              | thermal resistance<br>from junction to solder<br>point |             | [3] | -   | -   | 140 | K/W  |

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

<sup>[2]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm<sup>2</sup>.

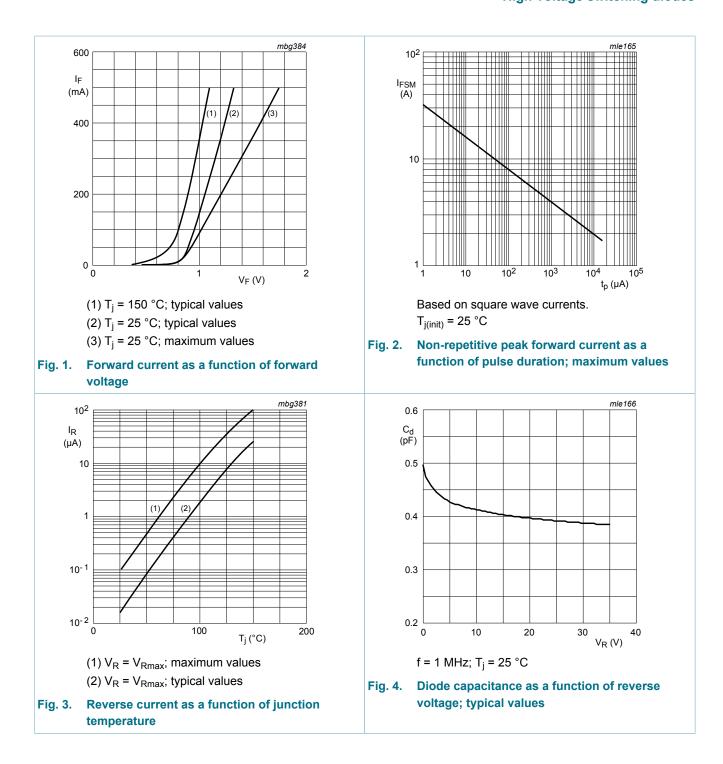
[3] Soldering point of cathode tab.

# **10. Characteristics**

| Table 7.     Characteristics   |                       |  |     |     |      |      |
|--------------------------------|-----------------------|--|-----|-----|------|------|
| Symbol                         | Parameter             | Conditions   | Min | Тур | Max  | Unit |
| Per diode                      |                       |  |     |     |      |      |
| V <sub>F</sub>                 | forward voltage       | I <sub>F</sub> = 100 mA; T <sub>amb</sub> = 25 °C  | -   | -   | 1    | V    |
|                                |                       | I <sub>F</sub> = 200 mA; T <sub>amb</sub> = 25 °C  | -   | -   | 1.25 | V    |
| I <sub>R</sub> reverse current | reverse current       | $V_R$ = 200 V; pulsed; t <sub>p</sub> ≤ 300 µs;<br>$\delta \le 0.02$ ; T <sub>amb</sub> = 25 °C  | -   | 25  | 100  | nA   |
|                                |                       | V <sub>R</sub> = 200 V; T <sub>j</sub> = 150 °C  | -   | -   | 100  | μA   |
| C <sub>d</sub>                 | diode capacitance     | f = 1 MHz; V <sub>R</sub> = 0 V; T <sub>amb</sub> = 25 °C  | -   | 0.6 | 5    | pF   |
| t <sub>rr</sub>                | reverse recovery time | $I_F$ = 30 mA; $I_R$ = 30 mA; $T_{amb}$ = 25 °C;<br>R <sub>L</sub> = 100 Ω; $I_{R(meas)}$ = 3 mA | -   | 16  | 50   | ns   |

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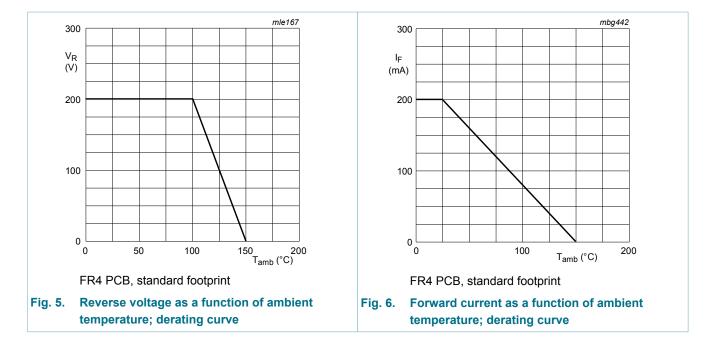
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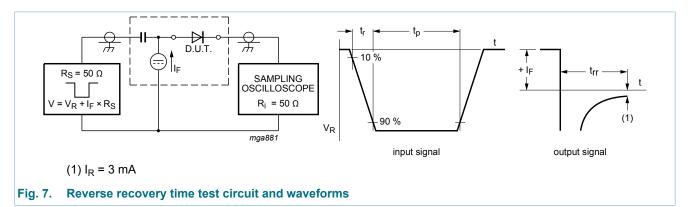
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# BAS21VD

### High-voltage switching diodes



## 11. Test information

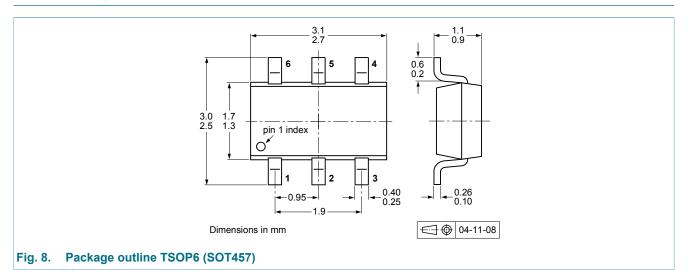


### **11.1 Quality information**

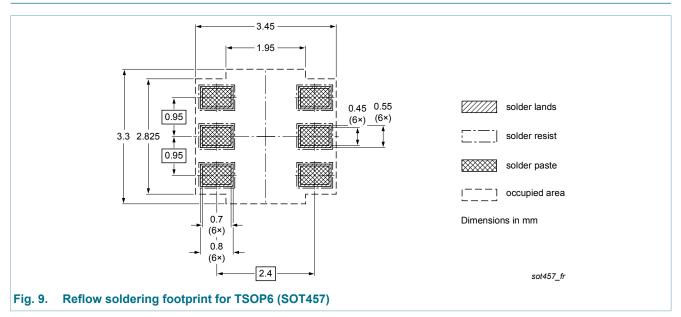
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

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### 12. Package outline



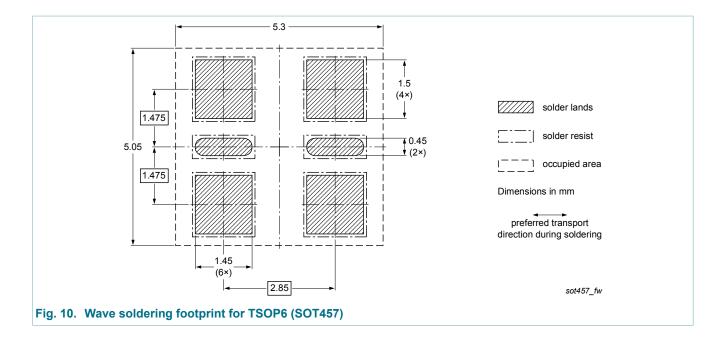
# 13. Soldering



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# 14. Revision history

| Table 8. Revision his | story   |                    |               |             |  |  |
|-----------------------|---|--------------------|---------------|-------------|--|--|
| Data sheet ID         | Release date  | Data sheet status  | Change notice | Supersedes  |  |  |
| BAS21VD v.3           | 20130801  | Product data sheet | -             | BAS21VD v.2 |  |  |
| Modifications:        | <ul> <li>Table 7. Characteristics: parameter unit of V<sub>F</sub> corrected</li> <li>Packing information: removed</li> <li>Legal information: updated</li> </ul> |                    |               |             |  |  |
| BAS21VD v.2           | 20110629  | Product data sheet | -             | BAS21VD v.1 |  |  |
| BAS21VD v.1           | 20030703  | Product data sheet | -             | -           |  |  |

#### High-voltage switching diodes

### 15. Legal information

#### 15.1 Data sheet status

| Document status [1][2]               | Product<br>status [ <u>3]</u> | Definition  |
|--------------------------------------|-------------------------------|---|
| Objective<br>[short] data<br>sheet   | Development                   | This document contains data from<br>the objective specification for product<br>development. |
| Preliminary<br>[short] data<br>sheet | Qualification                 | This document contains data from the preliminary specification.                             |
| Product<br>[short] data<br>sheet     | Production                    | This document contains the product specification.   |

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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